

Erratum

Corrections to "Analytical Model for Threshold Voltage Shift Due to Impurity Penetration Through a Thin Gate Oxide"

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In the above paper,¹ please note the following corrections.

We introduced the integral function having subscript n , H_n , as

$$H_n(\xi) = \frac{2}{\sqrt{\pi}} \frac{1}{n\xi} \int_0^\infty s^n \exp[-(s + \xi)^2] ds. \quad (30)$$

The corresponding Fig. 1 in the paper should be replaced by the following.

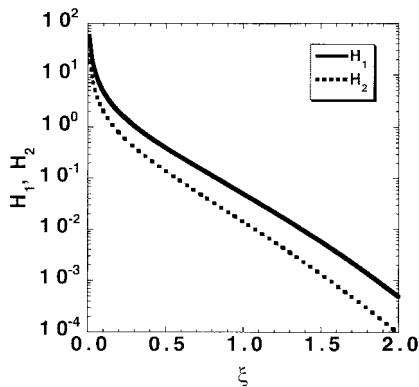


Fig. 1. Dependence of H_n on ξ : d_{ox}/L_{ox} .

The diffusion coefficient of boron in Si expressed by (36) in the paper should read

$$D_{Si}(B) = 0.76 \exp\left[-\frac{3.46(\text{eV})}{k_B T}\right] \text{cm}^2/\text{s}. \quad (36)$$

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¹K. Suzuki, *IEEE Trans. Electron Devices*, vol. 44, pp. 1386–1392, Sept. 1997.